L Number	Hits	Search Text	DB	Time stamp
17	7657	"alignment mark" or Halignment adj mark)	USPAT; EPO; JPO; IBM TDB	03:54   503\08:03
21	21294	"chemical mechanical polishing" or CMP	USPAT; EFO; JPO; IEM TIB	2003/66 03 09:32
22	33	<pre>(("magnetoresistive random access memory" or MRAM) and ("silicon oxide" or SiO or dielectric or insulating, and (Copper or Du) and (channels or vias or trench or openings))) and ("chemical mechanical polishing" or CMP)</pre>	USTAT; BIC; JPO; IBM_TIB	2003/64,03 04:30
20	113	("magnetoresistive random access memory" or MRAM) and (("silicon oxide" or SiO or dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings))	USFAT; EFD; JPO; IBM_TIB	2 103 106,103 1 x:21
31	112	of dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings) and ("magnetoresistive random access memory" or MRAM)	USPAT; EPO; JPO; IEM_TIB	2003 06/03 11:30
16	568	"magnetoresistive random actess memory" or MRAM	USPAT; EPO; JPO; IPM TIB	2:03:06:03 1:37
3 4	511	("alignment mark" or (alignment adj mark): and (Copper or Cu) and (channels or vias or trench or openings)	USPĀT; EPO; JPO; IEM TIB	2:03/06/03 10:34
35	144	("magnetoresistive random access memory" or MRAM) and (Copper or Cu) and (channels or vias or trench or openings)	USFAT; EFC; JPC; IBM TDB	2 +03 106,103 1 :39
19	68271	("silicon oxide" or SiO or dielectric or insulating) and (Copper or Cu) and (Channels or Vias or trench or openings)	USFAT; EFG; JPG; IBM TDB	2 03/06/03 1 :52
36	4445	("chemical mechanical polishing" or CMP) and (("silicon oxide" or SiO or dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings)) and etch\$3	USTAT; EFI; JPC; IEM_TIB	2:03:06/03 10:53
37	4798	("chemical mechanical polishing" or CMP) and (("silicon oxide" or SiO or dielectric or insulating) and (Copper or Cu) and (channels or vias or trench or openings))	USFAT; EFC; JPC; IFM_TDB	2003/06/03 10:55
38	378	("magnetoresistive random access memory" or MRAM) and (channels or openings or windows or trench or vias or contact)	USFAT; EFC; JPC; IEM TDB	2003/06/03 10:57
39	46	(("magnetoresistive random access memory" or MRAM) and (channels or openings or windows or trench or vias or contact)) and 43%/(0.0018.	USFĀT; EPO; JPC; IBM_TDB	2003/06/03 10:57